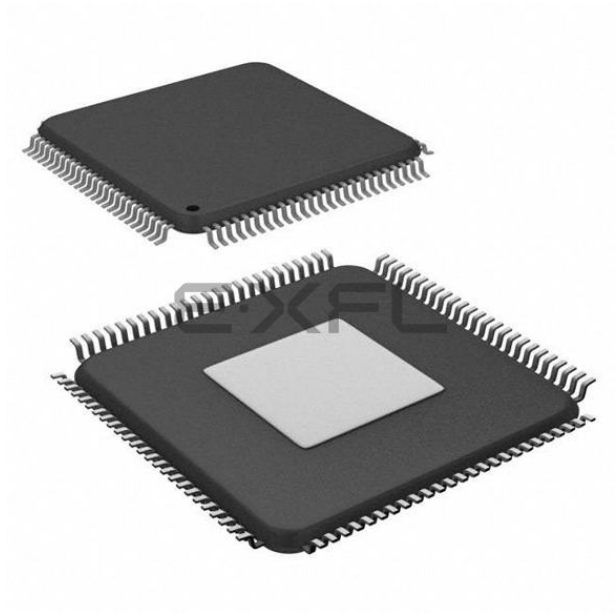
Infineon Technologies - XMC4400F100F256BAXQMA1 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, Ethernet, I²C, LINbus, SPI, UART, USB
Peripherals	DMA, I²S, LED, POR, PWM, WDT
Number of I/O	55
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	80K x 8
Voltage - Supply (Vcc/Vdd)	3.13V ~ 3.63V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP Exposed Pad
Supplier Device Package	PG-LQFP-100-25
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xmc4400f100f256baxqma1

1 Summary of Features

The XMC4400 devices are members of the XMC4000 Family of microcontrollers based on the ARM Cortex-M4 processor core. The XMC4000 is a family of high performance and energy efficient microcontrollers optimized for Industrial Connectivity, Industrial Control, Power Conversion, Sense & Control.

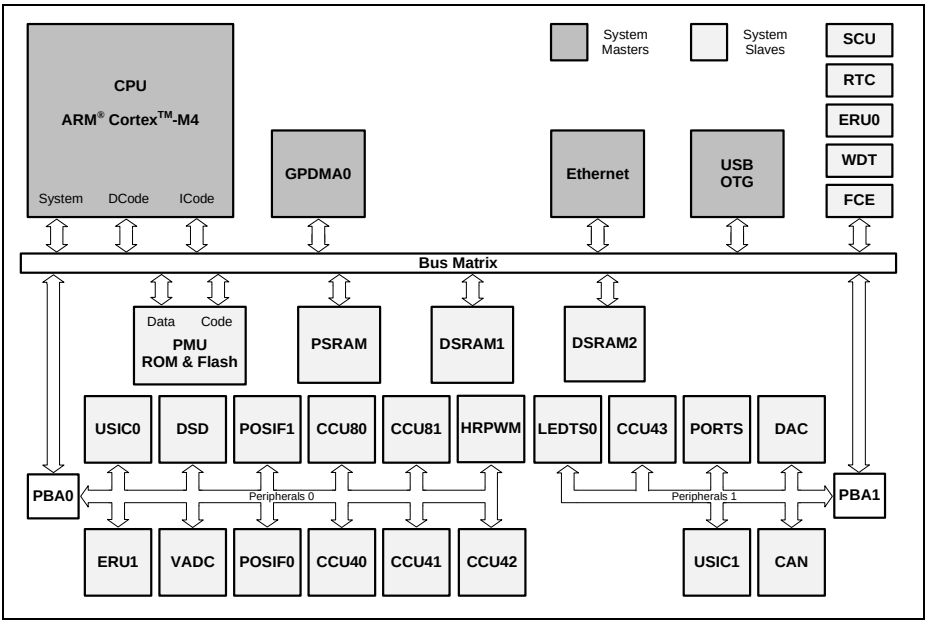

Figure 1 System Block Diagram

CPU Subsystem

- CPU Core
  - High Performance 32-bit ARM Cortex-M4 CPU
  - 16-bit and 32-bit Thumb2 instruction set
  - DSP/MAC instructions
  - System timer (SysTick) for Operating System support
- Floating Point Unit
- Memory Protection Unit
- Nested Vectored Interrupt Controller
- One General Purpose DMA with up-to 8 channels
- Event Request Unit (ERU) for programmable processing of external and internal service requests
- Flexible CRC Engine (FCE) for multiple bit error detection

Table 4 Features of XMC4400 Device Types

Derivative[1)]	ADC Chan.	DSD Chan.	DAC Chan.	CCU4 Slice	CCU8 Slice	POSIF Intf.	HRPWM Intf.
XMC4400-F100x512	24	4	2	4 x 4	2 x 4	2	1
XMC4400-F64x512	14	4	2	4 x 4	2 x 4	2	1
XMC4400-F100x256	24	4	2	4 x 4	2 x 4	2	1
XMC4400-F64x256	14	4	2	4 x 4	2 x 4	2	1
XMC4402-F100x256	24	4	2	4 x 4	2 x 4	2	1
XMC4402-F64x256	14	4	2	4 x 4	2 x 4	2	1

1) x is a placeholder for the supported temperature range.

1.5 Definition of Feature Variants

The XMC4400 types are offered with several memory sizes and number of available VADC channels. **Table 5** describes the location of the available Flash memory, **Table 6** describes the location of the available SRAMs, **Table 7** the available VADC channels.

Table 5 Flash Memory Ranges

Total Flash Size	Cached Range	Uncached Range
256 Kbytes	$0800\ 0000_H$ – $0803\ FFFF_H$	$0C00\ 0000_H$ – $0C03\ FFFF_H$
512 Kbytes	$0800\ 0000_H$ – $0807\ FFFF_H$	$0C00\ 0000_H$ – $0C07\ FFFF_H$

Table 6 SRAM Memory Ranges

Total SRAM Size	Program SRAM	System Data SRAM	Communication Data SRAM
80 Kbytes	$1FFF\ C000_H$ – $1FFF\ FFFF_H$	$2000\ 0000_H$ – $2000\ 7FFF_H$	$2000\ 8000_H$ – $2000\ FFFF_H$

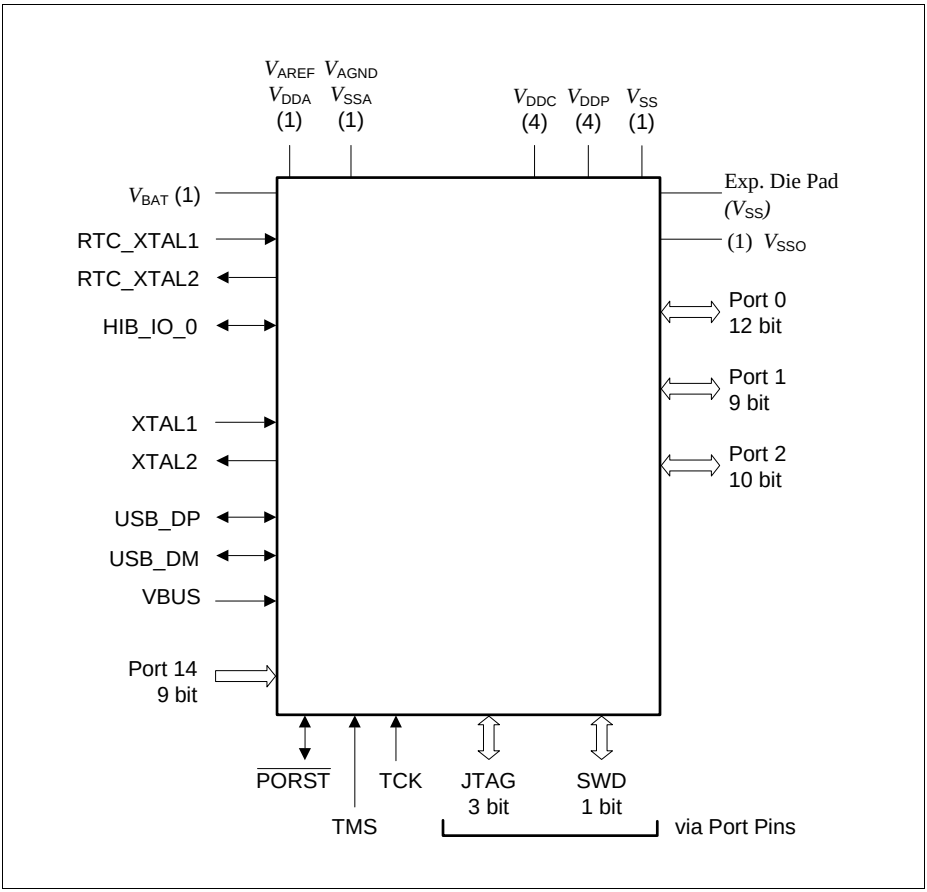

Figure 3 XMC4400 Logic Symbol PG-LQFP-64 and PG-TQFP-64

2.2 Pin Configuration and Definition

The following figures summarize all pins, showing their locations on the different packages.

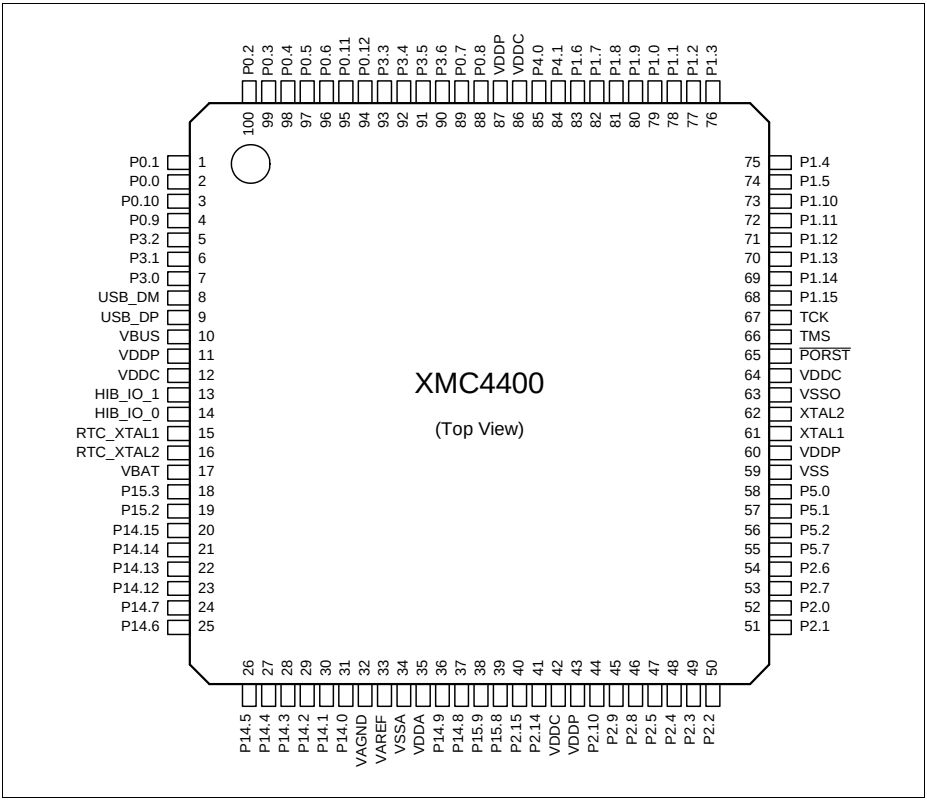

Figure 4 XMC4400 PG-LQFP-100 Pin Configuration (top view)

Table 10 Package Pin Mapping (cont'd)

Function	LQFP-100	LQFP-64 TQFP-64	Pad Type	Notes
VDDA/VAREF	-	22	AN_Power/AN_Ref	Shared analog supply and reference voltage pin.
VSSA	34	-	AN_Power	
VSSA/VAGND	-	21	AN_Power/AN_Ref	Shared analog supply and reference ground pin.
VDDC	12	9	Power	
VDDC	42	25	Power	
VDDC	64	42	Power	
VDDC	86	55	Power	
VDDP	11	8	Power	
VDDP	43	26	Power	
VDDP	60	38	Power	
VDDP	87	56	Power	
VSS	59	37	Power	
VSSO	63	41	Power	
VSS	Exp. Pad	Exp. Pad	Power	**Exposed Die Pad** The exposed die pad is connected internally to VSS. For proper operation, it is mandatory to connect the exposed pad directly to the common ground on the board. For thermal aspects, please refer to the Data Sheet. Board layout examples are given in an application note.

Table 15 PN-Junction Characterisitics for positive Overload

Pad Type	I_{OV} = 5 mA, T_J = -40 °C	I_{OV} = 5 mA, T_J = 150 °C
A1 / A1+	$V_{IN} = V_{DDP}$ + 1.0 V	$V_{IN} = V_{DDP}$ + 0.75 V
A2	$V_{IN} = V_{DDP}$ + 0.7 V	$V_{IN} = V_{DDP}$ + 0.6 V
AN/DIG_IN	$V_{IN} = V_{DDP}$ + 1.0 V	$V_{IN} = V_{DDP}$ + 0.75 V

Table 16 PN-Junction Characterisitics for negative Overload

Pad Type	I_{OV} = 5 mA, T_J = -40 °C	I_{OV} = 5 mA, T_J = 150 °C
A1 / A1+	$V_{IN} = V_{SS}$ - 1.0 V	$V_{IN} = V_{SS}$ - 0.75 V
A2	$V_{IN} = V_{SS}$ - 0.7 V	$V_{IN} = V_{SS}$ - 0.6 V
AN/DIG_IN	$V_{IN} = V_{DDP}$ - 1.0 V	$V_{IN} = V_{DDP}$ - 0.75 V

Table 17 Port Groups for Overload and Short-Circuit Current Sum Parameters

Group	Pins
1	P0.[12:0], P3.[6:0]
2	P14.[15:0], P15.[9:2]
3	P2.[15:0], P5.[7:0]
4	P1.[15:0], P4.[1:0]

3.1.4 Pad Driver and Pad Classes Summary

This section gives an overview on the different pad driver classes and its basic characteristics. More details (mainly DC parameters) are defined in the **Section 3.2.1**.

Table 18 Pad Driver and Pad Classes Overview

Class	Power Supply	Type	Sub-Class	Speed Grade	Load	Termination
A	3.3 V	LVTTL I/O, LVTTL outputs	**A1** (e.g. GPIO)	6 MHz	100 pF	No
			A1+ (e.g. serial I/Os)	25 MHz	50 pF	Series termination recommended
			A2 (e.g. ext. Bus)	80 MHz	15 pF	Series termination recommended

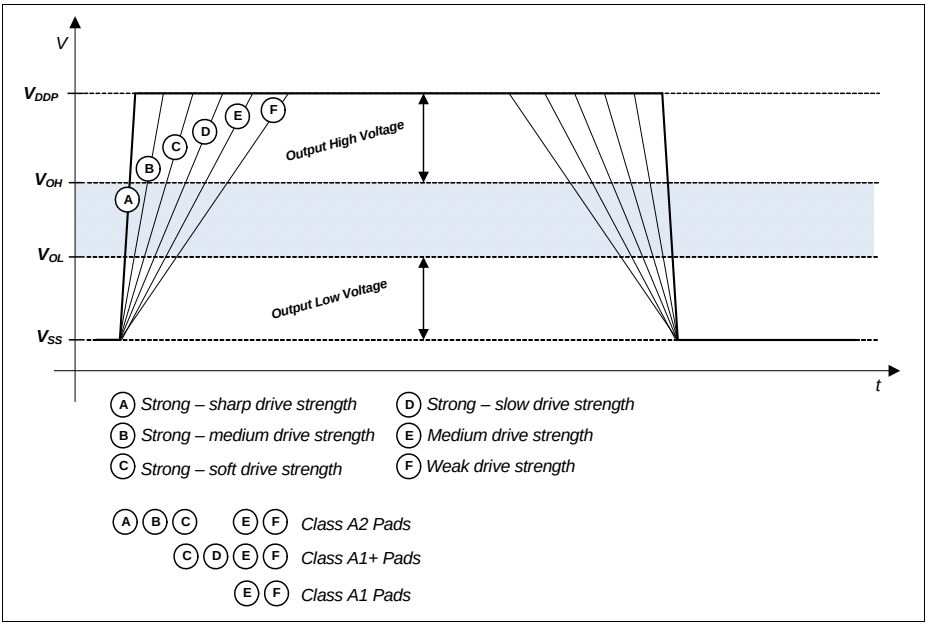

Figure 10 Output Slopes with different Pad Driver Modes

Figure 10 is a qualitative display of the resulting output slope performance with different output driver modes. The detailed input and output characteristics are listed in **Section 3.2.1**.

Table 21 Standard Pads Class_A1

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.		Max.		
Input leakage current	I_{OZA1} CC	-500		500	nA	0 V ≤ V_{IN} ≤ V_{DDP}
Input high voltage	V_{IHA1} SR	0.6 × V_{DDP}		V_{DDP} + 0.3	V	max. 3.6 V
Input low voltage	V_{ILA1} SR	-0.3		0.36 × V_{DDP}	V	
Output high voltage, POD[1] = weak	V_{OHA1} CC	V_{DDP} - 0.4		–	V	I_{OH} ≥ -400 µA
		2.4		–	V	I_{OH} ≥ -500 µA
Output high voltage, POD[1] = medium		V_{DDP} - 0.4		–	V	I_{OH} ≥ -1.4 mA
		2.4		–	V	I_{OH} ≥ -2 mA
Output low voltage	V_{OLA1} CC	–		0.4	V	I_{OL} ≤ 500 µA; POD[1] = weak
		–		0.4	V	I_{OL} ≤ 2 mA; POD[1] = medium
Fall time	t_{FA1} CC	–		150	ns	C_L = 20 pF; POD[1] = weak
		–		50	ns	C_L = 50 pF; POD[1] = medium
Rise time	t_{RA1} CC	–		150	ns	C_L = 20 pF; POD[1] = weak
		–		50	ns	C_L = 50 pF; POD[1] = medium

1) POD = Pin Out Driver

Table 22 Standard Pads Class_A1+

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.		Max.		
Input leakage current	I_{OZA1+} CC	-1		1	µA	0 V ≤ V_{IN} ≤ V_{DDP}
Input high voltage	V_{IHA1+} SR	0.6 × V_{DDP}		V_{DDP} + 0.3	V	max. 3.6 V
Input low voltage	V_{ILA1+} SR	-0.3		0.36 × V_{DDP}	V	

3.2.3 Digital to Analog Converters (DACx)

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 27 DAC Parameters (Operating Conditions apply)

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
RMS supply current	I_{DD}	CC	–	2.5	4	mA	per active DAC channel, without load currents of DAC outputs
Resolution	RES	CC	–	12	–	Bit	
Update rate	f_{URATE_A}	CC	–		2	Msample/s	data rate, where DAC can follow 64 LSB code jumps to ± 1LSB accuracy
Update rate	f_{URATE_F}	CC	–		5	Msample/s	data rate, where DAC can follow 64 LSB code jumps to ± 4 LSB accuracy
Settling time	t_{SETTLE}	CC	–	1	2	µs	at full scale jump, output voltage reaches target value ± 20 LSB
Slew rate	SR	CC	2	5	–	V/µs	
Minimum output voltage	V_{OUT_MIN}	CC	–	0.3	–	V	code value unsigned: 000_H; signed: 800_H
Maximum output voltage	V_{OUT_MAX}	CC	–	2.5	–	V	code value unsigned: FFF_H; signed: $7FF_H$
Integral non-linearity[1)]	INL	CC	-5.5	±2.5	5.5	LSB	$R_L \geq 5$ kOhm, $C_L \leq 50$ pF
Differential non-linearity	DNL	CC	-2	±1	2	LSB	$R_L \geq 5$ kOhm, $C_L \leq 50$ pF

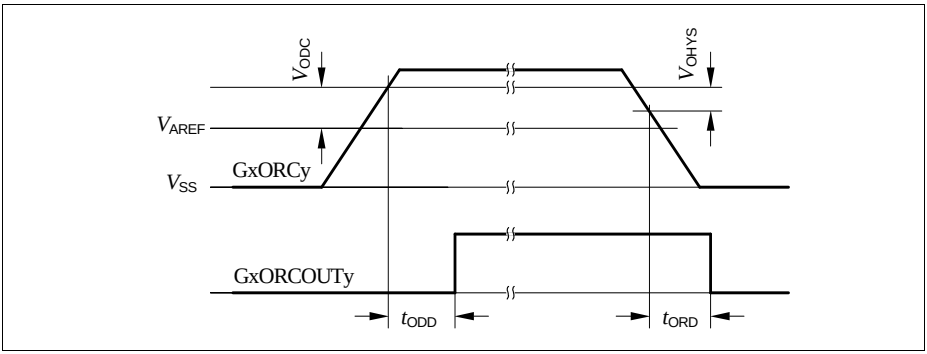

Figure 16 GxORCOUTy Trigger Generation

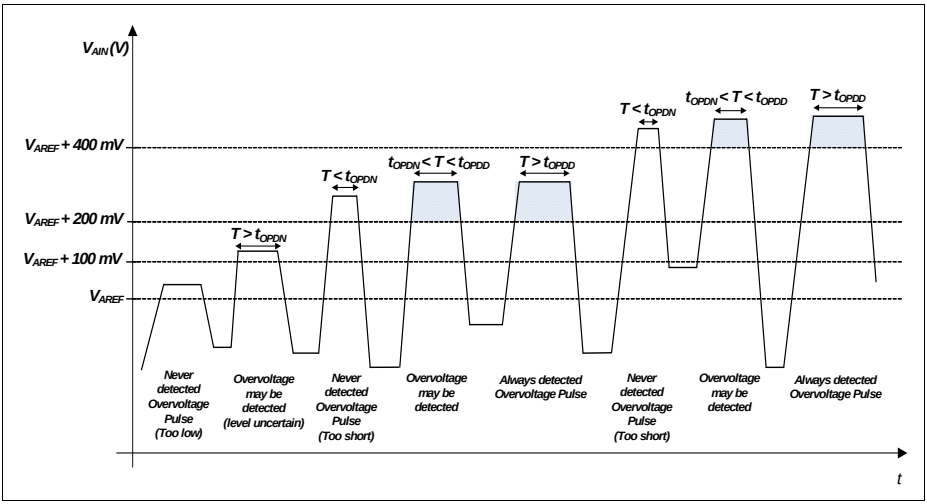

Figure 17 ORC Detection Ranges

Table 30 CMP and 10-bit DAC characteristics (Operating Conditions apply) (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
CSG Output Jitter	D_{CSG} CC	–	–	1	clk	
Bias startup time	t_{start} CC	–	–	98	us	
Bias supply current	I_{DDbias} CC	–	–	400	µA	
CSGy startup time	t_{CSGS} CC	–	–	2	µs	
Input operation current[1]	I_{DDCIN} CC	-10	–	33	µA	See **Figure 19**
High Speed Mode						
DAC output voltage range	V_{DOUT} CC	V_{SS}	–	V_{DDP}	V	
DAC propagation delay - Full scale	t_{FShs} CC	–	–	80	ns	See **Figure 20**
Input Selector propagation delay - Full scale	t_{Dhs} CC	–	–	100	ns	See **Figure 20**
Comparator bandwidth	t_{Dhs} CC	20	–	–	ns	
DAC CLK frequency	f_{clk} SR	–	–	30	MHz	
Supply current	I_{DDhs} CC	–	–	940	µA	
Low Speed Mode						
DAC output voltage range	V_{DOUT} CC	$0.1 \times V_{DDP}$[2]	–	V_{DDP}	V	
DAC propagation delay - Full Scale	t_{FSls} CC	–	–	160	ns	See **Figure 20**
Input Selector propagation delay - Full Scale	t_{Dls} CC	–	–	200	ns	See **Figure 20**
Comparator bandwidth	t_{Dls} CC	20	–	–	ns	
DAC CLK frequency	f_{clk} SR	–	–	30	MHz	
Supply current	I_{DDls} CC	–	–	300	µA	

1) Typical input resistance R_{CIN} = 100kOhm.

3.2.8 USB OTG Interface DC Characteristics

The Universal Serial Bus (USB) Interface is compliant to the USB Rev. 2.0 Specification and the OTG Specification Rev. 1.3. High-Speed Mode is not supported.

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 35 USB OTG VBUS and ID Parameters (Operating Conditions apply)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
VBUS input voltage range	V_{IN} CC	0.0	–	5.25	V	
A-device VBUS valid threshold	V_{B1} CC	4.4	–	–	V	
A-device session valid threshold	V_{B2} CC	0.8	–	2.0	V	
B-device session valid threshold	V_{B3} CC	0.8	–	4.0	V	
B-device session end threshold	V_{B4} CC	0.2	–	0.8	V	
VBUS input resistance to ground	R_{VBUS_IN} CC	40	–	100	kOhm	
B-device VBUS pull-up resistor	R_{VBUS_PU} CC	281	–	–	Ohm	Pull-up voltage = 3.0 V
B-device VBUS pull-down resistor	R_{VBUS_PD} CC	656	–	–	Ohm	
USB.ID pull-up resistor	R_{UID_PU} CC	14	–	25	kOhm	
VBUS input current	I_{VBUS_IN} CC	–	–	150	µA	$0\ V \le V_{IN} \le 5.25\ V$: T_{AVG} = 1 ms

Table 39 Power Supply Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Sleep supply current[3] Peripherals enabled Frequency: f_{CPU} / f_{PERIPH} / f_{CCU} in MHz	I_{DDPS} CC	–	104	–	mA	120 / 120 / 120
		–	93	–		120 / 60 / 60
		–	78	–		60 / 60 / 120
		–	57	–		24 / 24 / 24
		–	46	–		1 / 1 / 1
f_{CPU} / f_{PERIPH} / f_{CCU} in kHz		–	46	–		100 / 100 / 100
Sleep supply current[4] Peripherals disabled Frequency: f_{CPU} / f_{PERIPH} / f_{CCU} in MHz	I_{DDPS} CC	–	72	–	mA	120 / 120 / 120
		–	71	–		120 / 60 / 60
		–	61	–		60 / 60 / 120
		–	52	–		24 / 24 / 24
		–	46	–		1 / 1 / 1
f_{CPU} / f_{PERIPH} / f_{CCU} in kHz		–	46	–		100 / 100 / 100
Deep Sleep supply current[5] Flash in Sleep mode Frequency: f_{CPU} / f_{PERIPH} / f_{CCU} in MHz	I_{DDPD} CC	–	8	–	mA	24 / 24 / 24
		–	5	–		4 / 4 / 4
		–	4	–		1 / 1 / 1
f_{CPU} / f_{PERIPH} / f_{CCU} in kHz		–	4.5	–		100 / 100 / 100 [6]
Hibernate supply current RTC on[7]	I_{DDPH} CC	–	12.8	–	µA	V_{BAT} = 3.3 V
		–	9.0	–		V_{BAT} = 2.4 V
		–	7.7	–		V_{BAT} = 2.0 V
Hibernate supply current RTC off[8]	I_{DDPH} CC	–	12.0	–	µA	V_{BAT} = 3.3 V
		–	8.4	–		V_{BAT} = 2.4 V
		–	7.0	–		V_{BAT} = 2.0 V
Worst case active supply current[9]	I_{DDPA} CC	–	–	170 [10]	mA	V_{DDP} = 3.6 V, T_J = 150 °C
V_{DDA} power supply current	I_{DDA} CC	–	–	–[11]	mA	
I_{DDP} current at $\overline{\text{PORST}}$ Low	I_{DDP_PORST} CC	–	–	30	mA	V_{DDP} = 3.6 V, T_J = 150 °C

3.2.11 Flash Memory Parameters

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 41 Flash Memory Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Erase Time per 256 Kbyte Sector	t_{ERP} CC	–	5	5.5	s	
Erase Time per 64 Kbyte Sector	t_{ERP} CC	–	1.2	1.4	s	
Erase Time per 16 Kbyte Logical Sector	t_{ERP} CC	–	0.3	0.4	s	
Program time per page[1)]	t_{PRP} CC	–	5.5	11	ms	
Erase suspend delay	t_{FL_ErSusp} CC	–	–	15	ms	
Wait time after margin change	$t_{FL\_MarginDel}$ CC	10	–	–	µs	
Wake-up time	t_{WU} CC	–	–	270	µs	
Read access time	t_a CC	20	–	–	ns	For operation with $1 / f_{CPU} < t_a$ wait states must be configured[2)]
Data Retention Time, Physical Sector[3)4)]	t_{RET} CC	20	–	–	years	Max. 1000 erase/program cycles
Data Retention Time, Logical Sector[3)4)]	t_{RETL} CC	20	–	–	years	Max. 100 erase/program cycles

Table 41 Flash Memory Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Data Retention Time, User Configuration Block (UCB)[3)4)]	t_{RTU} CC	20	–	–	years	Max. 4 erase/program cycles per UCB
Endurance on 64 Kbyte Physical Sector PS4	N_{EPS4} CC	10000	–	–	cycles	BA-marking devices only! Cycling distributed over life time[5)]

1) In case the Program Verify feature detects weak bits, these bits will be programmed once more. The reprogramming takes an additional time of 5.5 ms.

2) The following formula applies to the wait state configuration: FCON.WSPFLASH × (1 / f_{CPU}) ≥ t_a.

3) Storage and inactive time included.

4) Values given are valid for an average weighted junction temperature of T_J = 110°C.

5) Only valid with robust EEPROM emulation algorithm, equally cycling the logical sectors. For more details see the Reference Manual.

Slow Internal Clock Source

Table 46 Slow Internal Clock Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Nominal frequency	f_{OSI} CC	–	32.768	–	kHz	
Accuracy	Δf_{OSI} CC	-4	–	4	%	V_{BAT} = const. 0 °C ≤ T_A ≤ 85 °C
		-5	–	5	%	V_{BAT} = const. T_A < 0 °C or T_A > 85 °C
		-5	–	5	%	2.4 V ≤ V_{BAT}, T_A = 25 °C
		-10	–	10	%	1.95 V ≤ V_{BAT} < 2.4 V, T_A = 25 °C
Start-up time	t_{OSIS} CC	–	50	–	µs	

3.3.7 Serial Wire Debug Port (SW-DP) Timing

The following parameters are applicable for communication through the SW-DP interface.

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Note: Operating conditions apply.

Table 48 SWD Interface Timing Parameters (Operating Conditions apply)

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
SWDCLK clock period	t_{SC}	SR	25	–	–	ns	C_L = 30 pF
			40	–	–	ns	C_L = 50 pF
SWDCLK high time	t_1	SR	10	–	500000	ns	
SWDCLK low time	t_2	SR	10	–	500000	ns	
SWDIO input setup to SWDCLK rising edge	t_3	SR	6	–	–	ns	
SWDIO input hold after SWDCLK rising edge	t_4	SR	6	–	–	ns	
SWDIO output valid time after SWDCLK rising edge	t_5	CC	–	–	17	ns	C_L = 50 pF
			–	–	13	ns	C_L = 30 pF
SWDIO output hold time from SWDCLK rising edge	t_6	CC	3	–	–	ns	

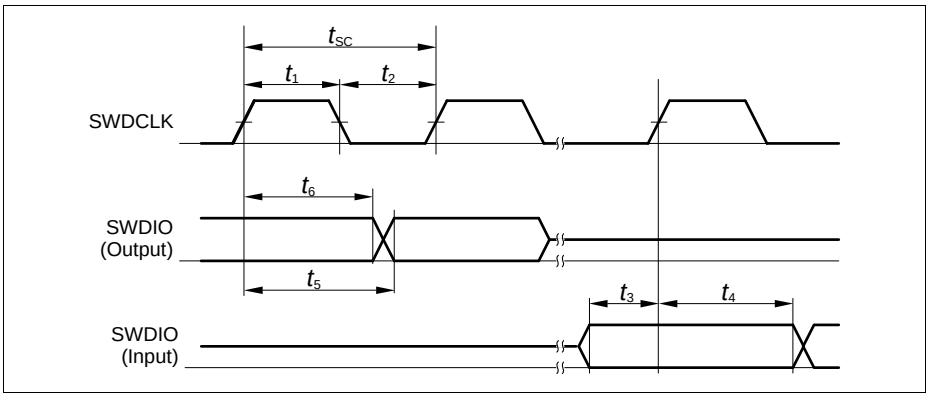

Figure 30 SWD Timing

Table 54 USIC IIC Fast Mode Timing[1)]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Fall time of both SDA and SCL	t_1 CC/SR	20 + 0.1*C_b [2)]	-	300	ns	
Rise time of both SDA and SCL	t_2 CC/SR	20 + 0.1*C_b [2)]	-	300	ns	
Data hold time	t_3 CC/SR	0	-	-	µs	
Data set-up time	t_4 CC/SR	100	-	-	ns	
LOW period of SCL clock	t_5 CC/SR	1.3	-	-	µs	
HIGH period of SCL clock	t_6 CC/SR	0.6	-	-	µs	
Hold time for (repeated) START condition	t_7 CC/SR	0.6	-	-	µs	
Set-up time for repeated START condition	t_8 CC/SR	0.6	-	-	µs	
Set-up time for STOP condition	t_9 CC/SR	0.6	-	-	µs	
Bus free time between a STOP and START condition	t_{10} CC/SR	1.3	-	-	µs	
Capacitive load for each bus line	C_b SR	-	-	400	pF	

1) Due to the wired-AND configuration of an IIC bus system, the port drivers of the SCL and SDA signal lines need to operate in open-drain mode. The high level on these lines must be held by an external pull-up device, approximalely 10 kOhm for operation at 100 kbit/s, approximately 2 kOhm for operation at 400 kbit/s.

2) C_b refers to the total capacitance of one bus line in pF.

5 Quality Declarations

The qualification of the XMC4400 is executed according to the JEDEC standard JESD47H.

Note: For automotive applications refer to the Infineon automotive microcontrollers.

Table 63 Quality Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Operation lifetime	t_{OP} CC	20	–	–	a	$T_J \leq 109°C$, device permanent on
ESD susceptibility according to Human Body Model (HBM)	V_{HBM} SR	–	–	2 000	V	EIA/JESD22-A114-B
ESD susceptibility according to Charged Device Model (CDM)	V_{CDM} SR	–	–	500	V	Conforming to JESD22-C101-C
Moisture sensitivity level	MSL CC	–	–	3	–	JEDEC J-STD-020D
Soldering temperature	T_{SDR} SR	–	–	260	°C	Profile according to JEDEC J-STD-020D

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